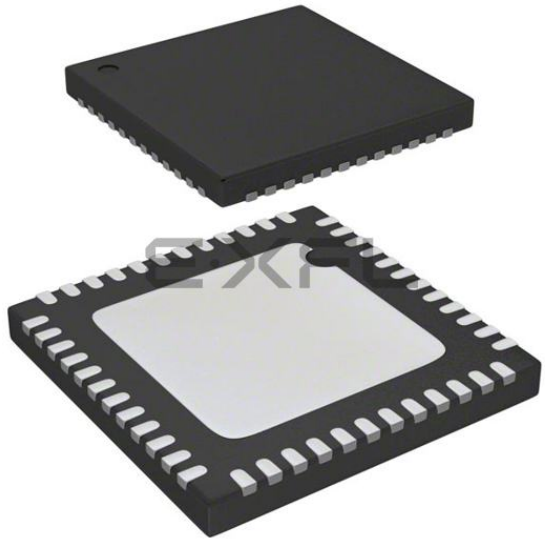

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	84MHz
Connectivity	I²C, IrDA, LINbus, SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	96K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f401ceu6

3.9 Nested vectored interrupt controller (NVIC)

The devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 62 maskable interrupt channels plus the 16 interrupt lines of the Cortex®-M4 with FPU.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

3.10 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 21 edge-detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 81 GPIOs can be connected to the 16 external interrupt lines.

3.11 Clocks and startup

On reset the 16 MHz internal RC oscillator is selected as the default CPU clock. The 16 MHz internal RC oscillator is factory-trimmed to offer 1% accuracy at 25 °C. The application can then select as system clock either the RC oscillator or an external 4-26 MHz clock source. This clock can be monitored for failure. If a failure is detected, the system automatically switches back to the internal RC oscillator and a software interrupt is generated (if enabled). This clock source is input to a PLL thus allowing to increase the frequency up to 84 MHz. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example if an indirectly used external oscillator fails).

Several prescalers allow the configuration of the two AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the two AHB buses is 84 MHz while the maximum frequency of the high-speed APB domains is 84 MHz. The maximum allowed frequency of the low-speed APB domain is 42 MHz.

The devices embed a dedicated PLL (PLLI2S) which allows to achieve audio class performance. In this case, the I^2S master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.

There are three power modes configured by software when the regulator is ON:

- MR is used in the nominal regulation mode (With different voltage scaling in Run)

  In Main regulator mode (MR mode), different voltage scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption.
- LPR is used in the Stop modes

  The LP regulator mode is configured by software when entering Stop mode.
- Power-down is used in Standby mode.

  The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost.

Depending on the package, one or two external ceramic capacitors should be connected on the V_{CAP_1} and V_{CAP_2} pins. The V_{CAP_2} pin is only available for the LQFP100 and UFBGA100 packages.

All packages have the regulator ON feature.

3.15.2 Regulator OFF

The Regulator OFF is available only on the UFBGA100, which features the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V12 voltage source through V_{CAP_1} and V_{CAP_2} pins.

Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to *Table 14: General operating conditions*.

The two 2.2 µF V_{CAP} ceramic capacitors should be replaced by two 100 nF decoupling capacitors. Refer to *Figure 18: Power supply scheme*.

When the regulator is OFF, there is no more internal monitoring on V12. An external power supply supervisor should be used to monitor the V12 of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V12 power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V12 logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.

Table 8. STM32F401xD/xE pin definitions (continued)

Pin Number					Pin name (function after reset)[1]	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN48	WLCSP49	LQFP64	LQFP100	UFBGA100						
-	-	39	65	E10	PC8	I/O	FT	-	USART6_CK, TIM3_CH3, SDIO_D0, EVENTOUT	-
-	-	40	66	D12	PC9	I/O	FT	-	I2S_CKIN, I2C3_SDA, TIM3_CH4, SDIO_D1, MCO_2, EVENTOUT	-
29	D1	41	67	D11	PA8	I/O	FT	-	I2C3_SCL, USART1_CK, TIM1_CH1, OTG_FS_SOF, MCO_1, EVENTOUT	-
30	D2	42	68	D10	PA9	I/O	FT	-	I2C3_SMBA, USART1_TX, TIM1_CH2, EVENTOUT	OTG_FS_VBUS
31	C2	43	69	C12	PA10	I/O	FT	-	USART1_RX, TIM1_CH3, OTG_FS_ID, EVENTOUT	-
32	C1	44	70	B12	PA11	I/O	FT	-	USART1_CTS, USART6_TX, TIM1_CH4, OTG_FS_DM, EVENTOUT	-
33	C3	45	71	A12	PA12	I/O	FT	-	USART1_RTS, USART6_RX, TIM1_ETR, OTG_FS_DP, EVENTOUT	-
34	B3	46	72	A11	PA13 (JTMS-SWDIO)	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
-	-	-	73	C11	VCAP2	S	-	-	-	-
35	B1	47	74	F11	VSS	S	-	-	-	-
36	-	48	75	G11	VDD	S	-	-	-	-
-	B2	-	-	-	VDD	S	-	-	-	-
37	A1	49	76	A10	PA14 (JTCK-SWCLK)	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
38	A2	50	77	A9	PA15 (JTDI)	I/O	FT	-	JTDI, SPI1_NSS, SPI3_NSS/I2S3_WS, TIM2_CH1/TIM2_ETR, JTDI, EVENTOUT	-
-	-	51	78	B11	PC10	I/O	FT	-	SPI3_SCK/I2S3_CK, SDIO_D2, EVENTOUT	-
-	-	52	79	C10	PC11	I/O	FT	-	I2S3ext_SD, SPI3_MISO, SDIO_D3, EVENTOUT	-
-	-	53	80	B10	PC12	I/O	FT	-	SPI3_MOSI/I2S3_SD, SDIO_CK, EVENTOUT	-
-	-	-	81	C9	PD0	I/O	FT	-	EVENTOUT	-

Table 8. STM32F401xD/xE pin definitions (continued)

Pin Number					Pin name (function after reset)[1]	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN48	WLCSP49	LQFP64	LQFP100	UFBGA100						
47	A6	63	99	-	VSS	S	-	-	-	-
-	B6	-	-	H3	PDR_ON	I	FT	-	-	-
48	A7	64	100	-	VDD	S	-	-	-	-

1. Function availability depends on the chosen device.
2. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:
   - The speed should not exceed 2 MHz with a maximum load of 30 pF.
   - These I/Os must not be used as a current source (e.g. to drive an LED).
3. Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F401xx reference manual.
4. FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
5. If the device is delivered in an UFBGA100 and the BYPASS_REG pin is set to VDD (Regulator off/internal reset ON mode), then PA0 is used as an internal Reset (active low)

Table 9. Alternate function mapping (continued)

Port		AF00	AF01	AF02	AF03	AF04	AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15
		SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/SPI2/ I2S2/SPI3/ I2S3/SPI4	SPI2/I2S2/ SPI3/ I2S3	SPI3/I2S3/ USART1/ USART2	USART6	I2C2/ I2C3	OTG1_FS		SDIO			
Port B	PB0	-	TIM1_CH2N	TIM3_CH3	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB1	-	TIM1_CH3N	TIM3_CH4	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB3	JTDO-SWO	TIM2_CH2	-	-	-	SPI1_SCK	SPI3_SCK/ I2S3_CK	-	-	I2C2_SDA	-	-	-	-	-	EVENT OUT
	PB4	JTRST	-	TIM3_CH1	-	-	SPI1_ MISO	SPI3_MISO	I2S3ext_S D	-	I2C3_SDA	-	-	-	-	-	EVENT OUT
	PB5	-	-	TIM3_CH2	-	I2C1_ SMBA	SPI1 _MOSI	SPI3_MOSI/ I2S3_SD	-	-	-	-	-	-	-	-	EVENT OUT
	PB6	-	-	TIM4_CH1	-	I2C1_SCL	-	-	USART1_ TX	-	-	-	-	-	-	-	EVENT OUT
	PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_ RX	-	-	-	-	-	-	-	EVENT OUT
	PB8	-	-	TIM4_CH3	TIM10_CH1	I2C1_SCL	-	-	-	-	-	-	-	SDIO_ D4	-	-	EVENT OUT
	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS/I 2S2_WS	-	-	-	-	-	-	SDIO_ D5	-	-	EVENT OUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK/I 2S2_CK	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB12	-	TIM1_BKIN	-	-	I2C2_ SMBA	SPI2_NSS/I 2S2_WS	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK/I 2S2_CK	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB14	-	TIM1_CH2N	-	-	-	SPI2_MISO	I2S2ext_SD	-	-	-	-	-	-	-	-	EVENT OUT
	PB15	RTC_ REFN	TIM1_CH3N	-	-	-	SPI2_MOSI /I2S2_SD	-	-	-	-	-	-	-	-	-	EVENT OUT

Table 9. Alternate function mapping (continued)

Port		AF00	AF01	AF02	AF03	AF04	AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15
		SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/SPI2/ I2S2/SPI3/ I2S3/SPI4	SPI2/I2S2/ SPI3/ I2S3	SPI3/I2S3/ USART1/ USART2	USART6	I2C2/ I2C3	OTG1_FS		SDIO			
Port D	PD0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD2	-	-	TIM3_ETR	-	-	-	-	-	-	-	-	-	SDIO_ CMD	-	-	EVENT OUT
	PD3	-	-	-	-	-	SPI2_SCK/ I2S2_CK	-	USART2_ CTS	--	-	-	-	-	-	-	EVENT OUT
	PD4	-	-	-	-	-	-	-	USART2_ RTS		-	-	-	-	-	-	EVENT OUT
	PD5	-	-	-	-	-	-	-	USART2_ TX	-	-	-	-	-	-	-	EVENT OUT
	PD6	-	-	-	-	-	SPI3_MOSI /I2S3_SD	-	USART2_ RX	-	-	-	-	-	-	-	EVENT OUT
	PD7	-	-	-	-	-	-	-	USART2_ CK	-	-	-	-	-	-	-	EVENT OUT
	PD8	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD9	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD10	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD11	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD12	-	-	TIM4_CH1	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD13	-	-	TIM4_CH2	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD14	-	-	TIM4_CH3	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PD15	-	-	TIM4_CH4	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT

Table 9. Alternate function mapping (continued)

Port		AF00	AF01	AF02	AF03	AF04	AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15
		SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/SPI2/ I2S2/SPI3/ I2S3/SPI4	SPI2/I2S2/ SPI3/ I2S3	SPI3/I2S3/ USART1/ USART2	USART6	I2C2/ I2C3	OTG1_FS		SDIO			
Port H	PH0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PH1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT

6.3 Operating conditions

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HCLK}	Internal AHB clock frequency	Power Scale3: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x01	0	-	60	MHz
		Power Scale2: Regulator ON, VOS[1:0] bits in PWR_CR register = 0x10	0	-	84	
f_{PCLK1}	Internal APB1 clock frequency		0	-	42	
f_{PCLK2}	Internal APB2 clock frequency		0	-	84	
V_{DD}	Standard operating voltage		1.7(1)	-	3.6	V
V_{DDA} (2)(3)	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V_{DD}(4)	1.7(1)	-	2.4	
	Analog operating voltage (ADC limited to 2.4 M samples)		2.4	-	3.6	
V_{BAT}	Backup operating voltage		1.65	-	3.6	
V_{12}	Regulator ON: 1.2 V internal voltage on V_{CAP_1}/V_{CAP_2} pins	VOS[1:0] bits in PWR_CR register = 0x01 Max frequency 60 MHz	1.08(5)	1.14	1.20(5)	
		VOS[1:0] bits in PWR_CR register = 0x10 Max frequency 84 MHz	1.20(5)	1.26	1.32(5)	
V_{12}	Regulator OFF: 1.2 V external voltage must be supplied on V_{CAP_1}/V_{CAP_2} pins	Max. frequency 60 MHz.	1.1	1.14	1.2	
		Max. frequency 84 MHz.	1.2	1.26	1.32	
V_{IN}	Input voltage on RST and FT pins(6)	$2\ V \leq V_{DD} \leq 3.6\ V$	–0.3	-	5.5	
		$V_{DD} \leq 2\ V$	–0.3	-	5.2	
	Input voltage on BOOT0 pin		0	-	9	
P_D	Maximum allowed package power dissipation for suffix 7(7)	UFQFPN48	-	-	625	mW
		WLCSP49	-	-	392	
		LQFP64	-	-	313	
		LQFP100	-	-	465	
		UFBGA100	-	-	323	

6.3.5 Embedded reset and power control block characteristics

The parameters given in *Table 19* are derived from tests performed under ambient temperature and V_{DD} supply voltage @ 3.3V.

Table 19. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	
		PLS[2:0]=101 (falling edge)	2.65	2.84	3.02	
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	
$V_{PVDhyst}$(2)	PVD hysteresis		-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60(1)	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	
$V_{PDRhyst}$(2)	PDR hysteresis		-	40	-	mV
V_{BOR1}	Brownout level 1 threshold	Falling edge	2.13	2.19	2.24	V
		Rising edge	2.23	2.29	2.33	
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	
		Rising edge	2.53	2.59	2.63	
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	
		Rising edge	2.85	2.92	2.97	
$V_{BORhyst}$(2)	BOR hysteresis		-	100	-	mV
$T_{RSTTEMPO}$(2)(3)	POR reset timing		0.5	1.5	3.0	ms

Table 22. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory- V_{DD} = 1.7 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in **Run mode**	External clock, all peripherals enabled(2)(3)	84	23.2	24.5	25.6	26.6	mA
			60	15.1	16.3	17.4	18.4	
			40	10.8	12.1	13.2	14.2	
			30	8.8	10.0	11.1	12.2	
			20	6.9	8.0	9.0	10.1	
		External clock, all peripherals disabled(3)	84	12.3	13.6	14.7	15.7	
			60	8.2	9.4	10.5	11.5	
			40	6.0	7.3	8.3	9.4	
			30	4.9	6.2	7.2	8.3	
			20	4.0	5.1	6.1	7.2	

1. Guaranteed by characterization, not tested in production unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
3. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

Table 23. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory - V_{DD} = 3.3 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in **Run mode**	External clock, all peripherals enabled(2)(3)	84	23.4	24.7	25.8	26.8	mA
			60	15.3	16.5	17.6	18.6	
			40	11.0	12.3	13.4	14.4	
			30	9.0	10.2	11.3	12.4	
			20	7.1	8.2	9.2	10.3	
		External clock, all peripherals disabled(3)	84	12.5	13.8	14.9	15.9	
			60	8.4	9.6	10.7	11.7	
			40	6.2	7.5	8.5	9.6	
			30	5.1	6.4	7.4	8.5	
			20	4.2	5.3	6.3	7.4	

1. Guaranteed by characterization, not tested in production unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
3. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

Table 33. Peripheral current consumption (continued)

Peripheral		I_{DD} (typ)	Unit
APB2 (up to 84MHz)	TIM1	5.71	µA/MHz
	TIM9	2.86	
	TIM10	1.79	
	TIM11	2.02	
	ADC1(2)	2.98	
	SPI1	1.19	
	USART1	3.10	
	USART6	2.86	
	SDIO	5.95	
	SPI4	1.31	
	SYSCFG	0.71	

1. I2SMOD bit set in SPI_I2SCFGR register, and then the I2SE bit set to enable I2S peripheral.
2. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.

6.3.7 Wakeup time from low-power modes

The wakeup times given in *Table 34* are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep modes: the wakeup event is WFE.
- WKUP (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

All timings are derived from tests performed under ambient temperature and V_{DD}=3.3 V.

Table 34. Low-power mode wakeup timings(1)

Symbol	Parameter	Min(1)	Typ(1)	Max(1)	Unit
$t_{WUSLEEP}$(2)	Wakeup from Sleep mode	-	4	6	CPU clock cycle
t_{WUSTOP}(2)	Wakeup from Stop mode, usage of main regulator	-	13.5	14.5	µs
	Wakeup from Stop mode, usage of main regulator, Flash memory in Deep power down mode	-	105	111	
	Wakeup from Stop mode, regulator in low power mode	-	21	33	
	Wakeup from Stop mode, regulator in low power mode, Flash memory in Deep power down mode	-	113	130	
$t_{WUSTDBY}$(2)(3)	Wakeup from Standby mode	-	314	407	µs

1. Guaranteed by characterization, not tested in production.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first instruction.
3. $t_{WUSTDBY}$ maximum value is given at –40 °C.

Table 36. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User External clock source frequency(1)		-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{f(LSE)}$	OSC32_IN high or low time(1)		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time(1)		-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance(1)		-	5	-	pF
$DuCy_{(LSE)}$	Duty cycle		30	-	70	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production.

Figure 22. High-speed external clock source AC timing diagram

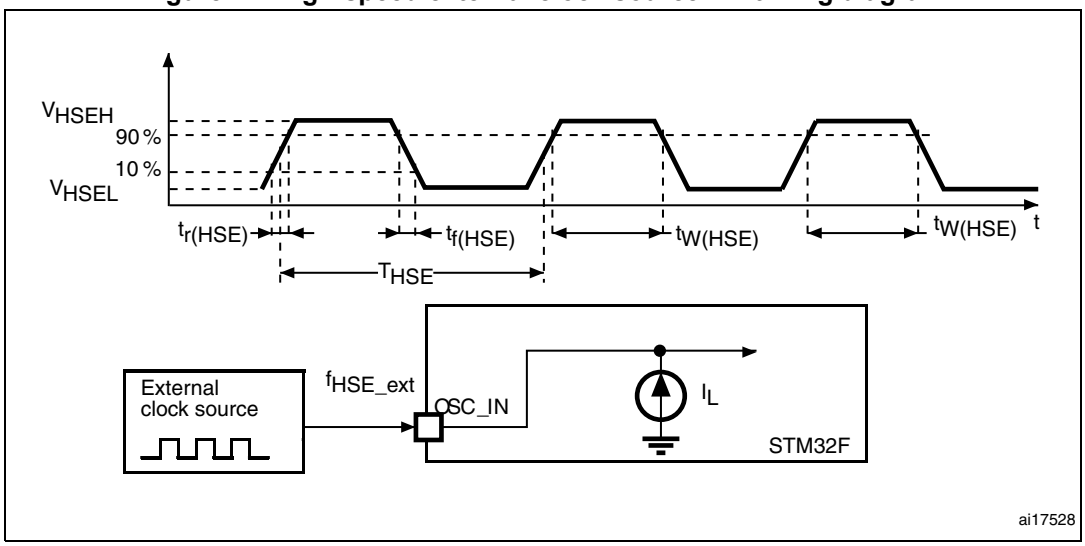


Figure 28 and *Figure 29* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 28. PLL output clock waveforms in center spread mode

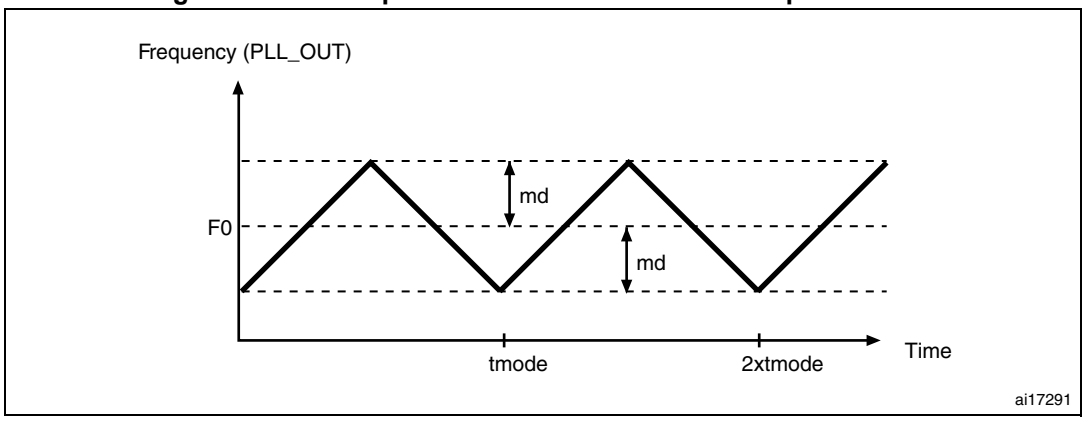
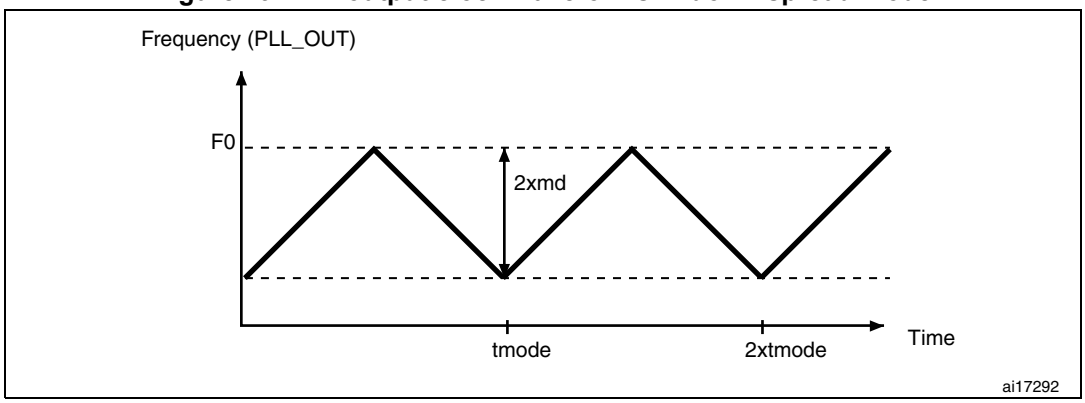


Figure 29. PLL output clock waveforms in down spread mode



6.3.12 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

Table 44. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DD}	Supply current	Write / Erase 8-bit mode, V_{DD} = 1.7 V	-	5	-	mA
		Write / Erase 16-bit mode, V_{DD} = 2.1 V	-	8	-	
		Write / Erase 32-bit mode, V_{DD} = 3.3 V	-	12	-	

Table 45. Flash memory programming

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	300	600	
		Program/erase parallelism (PSIZE) = x 32	-	250	500	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1200	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	700	1400	
		Program/erase parallelism (PSIZE) = x 32	-	550	1100	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.3	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	8	16	s
		Program/erase parallelism (PSIZE) = x 16	-	5.5	11	
		Program/erase parallelism (PSIZE) = x 32	-	4	8	
V_{prog}	Programming voltage	32-bit program operation	2.7	-	3.6	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.7	-	3.6	V

1. Guaranteed by characterization, not tested in production.
2. The maximum programming time is measured after 100K erase operations.

Table 46. Flash memory programming with V_{PP} voltage

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Double word programming	T_A = 0 to +40 °C V_{DD} = 3.3 V V_{PP} = 8.5 V	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time		-	230	-	ms
$t_{ERASE64KB}$	Sector (64 KB) erase time		-	490	-	
$t_{ERASE128KB}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	1.750	-	s

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 49. EMI characteristics for WLCSP49

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{CPU}]	Unit
				8/84 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, conforming to IEC61967-2	0.1 to 30 MHz	-4	dBµV
			30 to 130 MHz	-4	
			130 MHz to 1 GHz	-2	
			SAE EMI Level	1.5	-

Table 50. EMI characteristics for LQFP100

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{CPU}]	Unit
				8/84 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, conforming to IEC61967-2	0.1 to 30 MHz	19	dBµV
			30 to 130 MHz	19	
			130 MHz to 1 GHz	11	
			SAE EMI Level	3.5	-

6.3.14 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 53. I/O current injection susceptibility(1)

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0 pin	–0	NA	mA
	Injected current on NRST pin	–0	NA	
	Injected current on PB3, PB4, PB5, PB6, PB7, PB8, PB9, PC13, PC14, PC15, PH1, PDR_ON, PC0, PC1,PC2, PC3, PD1, PD5, PD6, PD7, PE0, PE2, PE3, PE4, PE5, PE6	–0	NA	
	Injected current on any other FT pin	–5	NA	
	Injected current on any other pins	–5	+5	

1. NA = not applicable.

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

6.3.16 I/O port characteristics

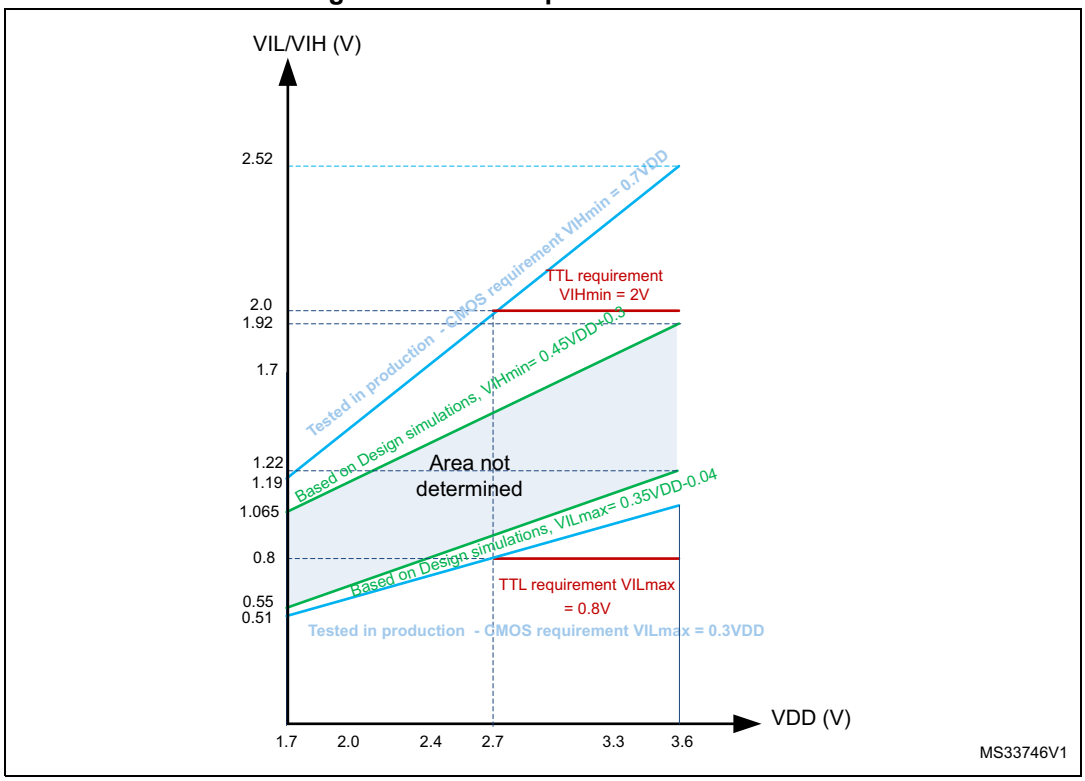
General input/output characteristics

Unless otherwise specified, the parameters given in *Table 54* are derived from tests performed under the conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 54. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	FT, and NRST I/O input low level voltage	1.7 V≤ V_{DD}≤ 3.6 V	-	-	$0.35V_{DD}–0.04$(1)	V
					$0.3V_{DD}$(2)	
	BOOT0 I/O input low level voltage	1.75 V≤ V_{DD} ≤ 3.6 V, -40 °C≤ T_A ≤ 105 °C	-	-	$0.1V_{DD}+0.1$	
		1.7 V≤ V_{DD} ≤ 3.6 V, 0 °C≤ T_A ≤ 105 °C	-	-		
V_{IH}	FT and NRST I/O input high level voltage(5)	1.7 V≤ V_{DD}≤ 3.6 V	$0.45V_{DD}+0.3$(1)	-	-	V
			$0.4V_{DD}$(2)			
	BOOT0 I/O input high level voltage	1.75 V≤ V_{DD} ≤ 3.6 V, -40 °C≤ T_A ≤ 105 °C	$0.17V_{DD}+0.7$(1)	-	-	
		1.7 V≤ V_{DD} ≤ 3.6 V, 0 °C≤ T_A ≤ 105 °C				

Figure 30. FT I/O input characteristics



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14 and PC15 which can sink or source up to ±3mA. When using the PC13 to PC15 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*. In particular:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 12*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 12*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 55* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 56. I/O AC characteristics[1][2] (continued)

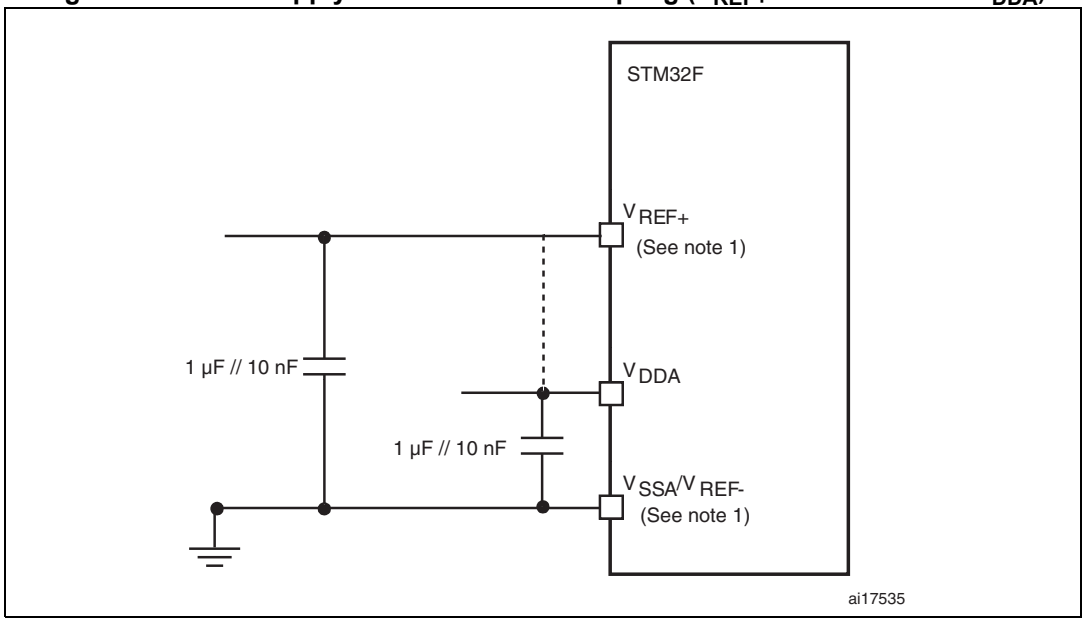
OSPEEDRy [1:0] bit value[1]	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
01	$f_{max(IO)out}$	Maximum frequency[3]	C_L = 50 pF, V_{DD} ≥ 2.70 V	-	-	25	MHz
			C_L = 50 pF, V_{DD} ≥ 1.7 V	-	-	12.5	
			C_L = 10 pF, V_{DD} ≥ 2.70 V	-	-	50	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	20	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} ≥2.7 V	-	-	10	ns
			C_L = 50 pF, V_{DD} ≥ 1.7 V	-	-	20	
			C_L = 10 pF, V_{DD} ≥ 2.70 V	-	-	6	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	10	
10	$f_{max(IO)out}$	Maximum frequency[3]	C_L = 40 pF, V_{DD} ≥ 2.70 V	-	-	50[4]	MHz
			C_L = 40 pF, V_{DD} ≥ 1.7 V	-	-	25	
			C_L = 10 pF, V_{DD} ≥ 2.70 V	-	-	100[4]	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	50[4]	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 40 pF, V_{DD}≥ 2.70 V	-	-	6	ns
			C_L = 40 pF, V_{DD}≥ 1.7 V	-	-	10	
			C_L = 10 pF, V_{DD}≥ 2.70 V	-	-	4	
			C_L = 10 pF, V_{DD}≥ 1.7 V	-	-	6	
11	$F_{max(IO)out}$	Maximum frequency[3]	C_L = 30 pF, V_{DD} ≥ 2.70 V	-	-	100[4]	MHz
			C_L = 30 pF, V_{DD} ≥ 1.7 V	-	-	50[4]	
			C_L = 10 pF, V_{DD} ≥ 2.70 V	-	-	180[4]	
			C_L = 10 pF, V_{DD}≥ 1.7 V	-	-	100[4]	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 30 pF, V_{DD} ≥ 2.70 V	-	-	4	ns
			C_L = 30 pF, V_{DD} ≥ 1.7 V	-	-	6	
			C_L = 10 pF, V_{DD}≥ 2.70 V	-	-	2.5	
			C_L = 10 pF, V_{DD}≥ 1.7 V	-	-	4	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller		10	-	-	ns

1. Guaranteed by characterization, not tested in production.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in *Figure 31*.
4. For maximum frequencies above 50 MHz and V_{DD} > 2.4 V, the compensation cell should be used.

General PCB design guidelines

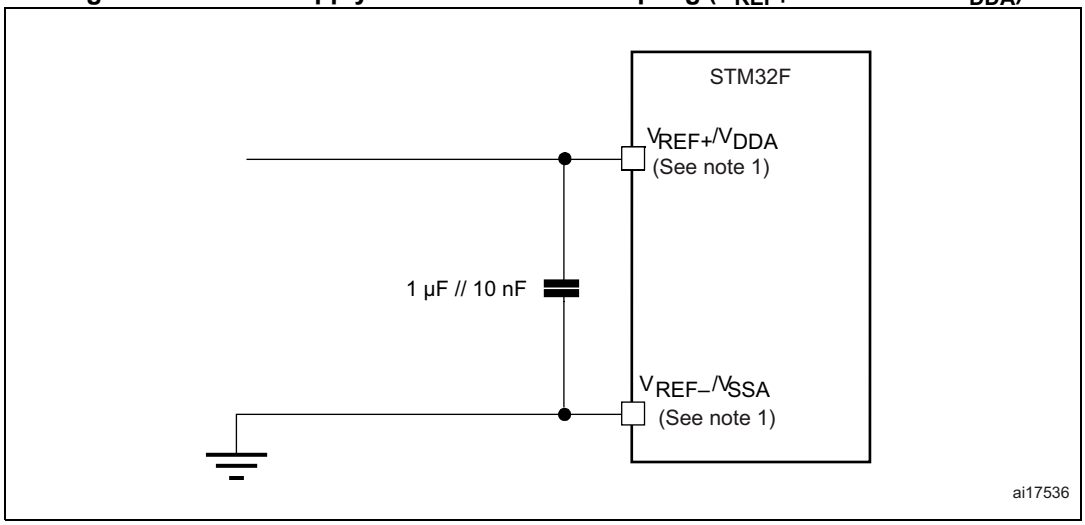
Power supply decoupling should be performed as shown in *Figure 42* or *Figure 43*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 42. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA100. V_{REF+} is also available on LQFP100. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

Figure 43. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA100. V_{REF+} is also available on LQFP100. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

Figure 45. SD default mode

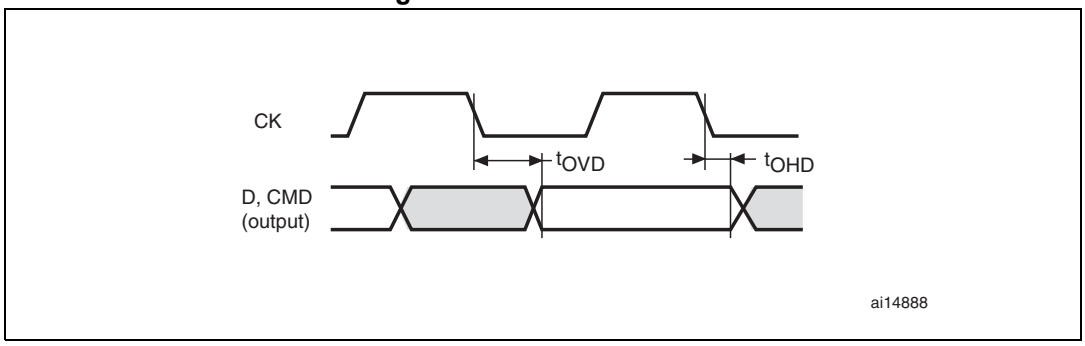


Table 77. Dynamic characteristics: SD / MMC characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode		0	-	48	MHz
-	SDIO_CK/fPCLK2 frequency ratio		-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp = 48MHz	8.5	9	-	ns
$t_{W(CKH)}$	Clock high time	fpp = 48MHz	8.3	10	-	
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t_{ISU}	Input setup time HS	fpp = 48MHz	3.5	-	-	ns
t_{IH}	Input hold time HS	fpp = 48MHz	0	-	-	
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t_{OV}	Output valid time HS	fpp = 48MHz	-	4.5	7	ns
t_{OH}	Output hold time HS	fpp = 48MHz	3	-	-	
CMD, D inputs (referenced to CK) in SD default mode						
t_{ISUD}	Input setup time SD	fpp = 24MHz	1.5	-	-	ns
t_{IHD}	Input hold time SD	fpp = 24MHz	0.5	-	-	
CMD, D outputs (referenced to CK) in SD default mode						
t_{OVD}	Output valid default time SD	fpp =24MHz	-	4.5	6.5	ns
t_{OHD}	Output hold default time SD	fpp =24MHz	3.5	-	-	

1. Data based on characterization results, not tested in production.
2. V_{DD} = 2.7 to 3.6 V.

6.3.25 RTC characteristics

Table 78. RTC characteristics

Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1}/RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-